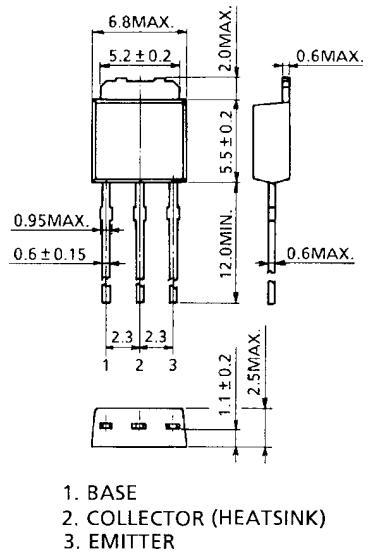
TOSHIBA Transistor Silicon PNP Triple Diffused Type

2SA1923

High Voltage Switching Applications

Unit: mm



JEDEC	—
JEITA	—
TOSHIBA	2-7B1A

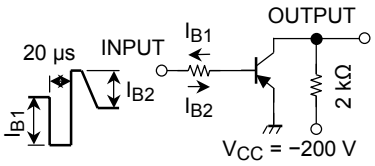
Weight: 0.36 g (typ.)

- High voltage: V_{CEO} = −400 V
- Low saturation voltage: $V_{CE\ (sat)}$ = −1 V (max)
  (I_C = −100 mA, I_B = −10 mA)

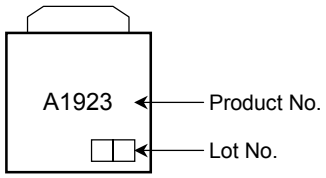
Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Collector-base voltage		V_{CBO}	−400	V
Collector-emitter voltage		V_{CEO}	−400	V
Emitter-base voltage		V_{EBO}	−7	V
Collector current	DC	I_C	−0.5	A
	Pulse	I_{CP}	−1	
Base current		I_B	−0.25	A
Collector power dissipation	Ta = 25°C	P_C	1	W
	Tc = 25°C		10	
Junction temperature		T_j	150	°C
Storage temperature range		T_{stg}	−55 to 150	°C

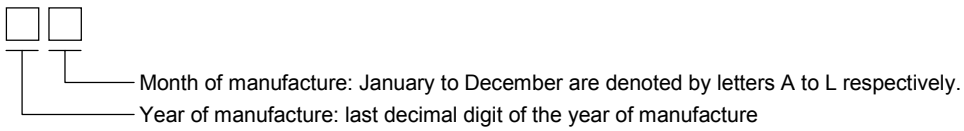
Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current		I_{CBO}	V_{CB} = −400 V, I_E = 0	—	—	−10	μA
Emitter cut-off current		I_{EBO}	V_{EB} = −7 V, I_C = 0	—	—	−1	μA
Collector-emitter breakdown voltage		$V_{(BR)\ CEO}$	I_C = −10 mA, I_B = 0	−400	—	—	V
DC current gain		$h_{FE\ (1)}$	V_{CE} = −5 V, I_C = −20 mA	140	—	450	
		$h_{FE\ (2)}$	V_{CE} = −5 V, I_C = −100 mA	140	—	400	
Collector-emitter saturation voltage		$V_{CE\ (sat)}$	I_C = −100 mA, I_B = −10 mA	—	−0.4	−1.0	V
Base-emitter saturation voltage		$V_{BE\ (sat)}$	I_C = −100 mA, I_B = −10 mA	—	−0.76	−0.9	V
Transition frequency		f_T	V_{CE} = −5 V, I_C = −50 mA	—	35	—	MHz
Collector output capacitance		C_{ob}	V_{CB} = −10 V, I_E = 0, f = 1 MHz	—	18	—	pF
Switching time	Turn-on time	t_{on}		—	0.2	—	μs
	Storage time	t_{stg}		—	2.3	—	
	Fall time	t_f	I_{B1} = −10 mA, I_{B2} = 20 mA, DUTY CYCLE ≤ 1%	—	0.2	—	

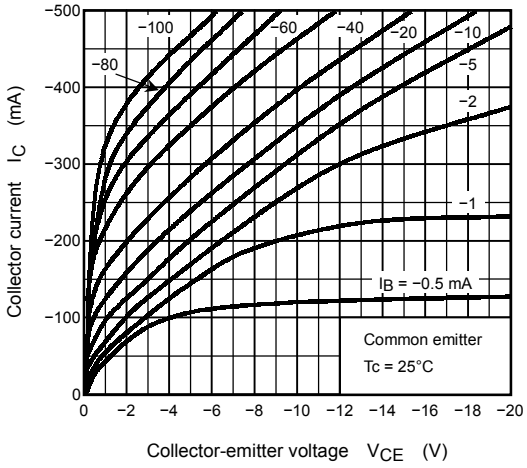
Marking



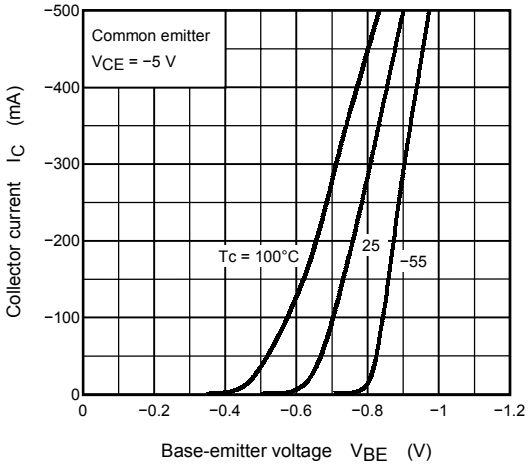
Explanation of Lot No.



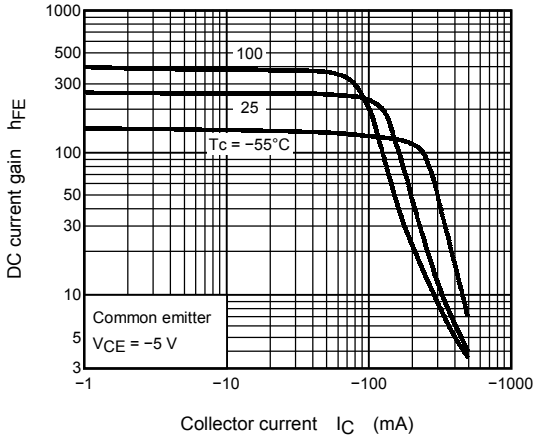
$I_C - V_{CE}$



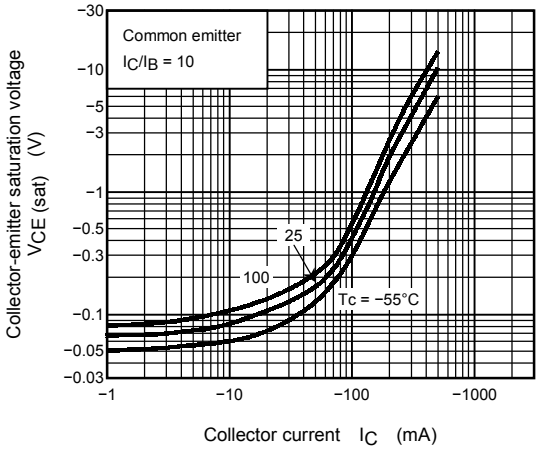
$I_C - V_{BE}$



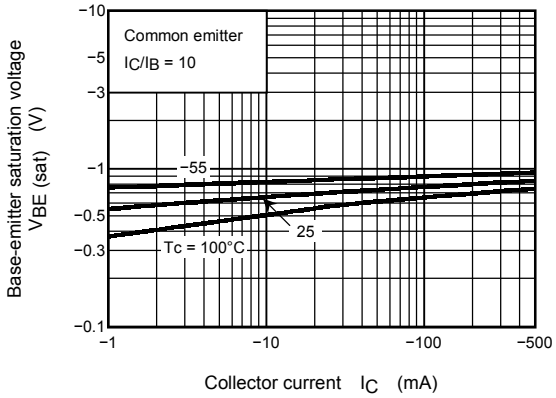
$h_{FE} - I_C$



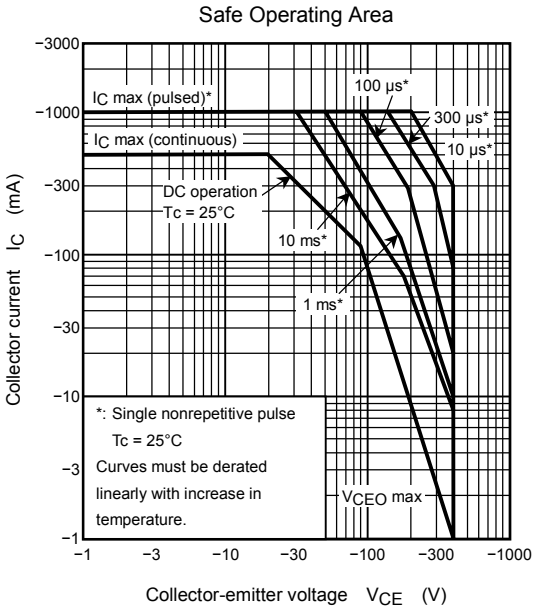
$V_{CE\ (sat)} - I_C$



$V_{BE\ (sat)} - I_C$



Safe Operating Area



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